UP1496

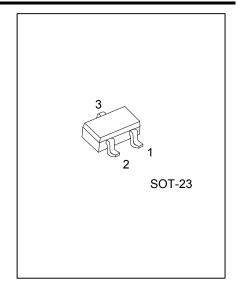
**Preliminary** 

## PNP SILICON TRANSISTOR

# PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

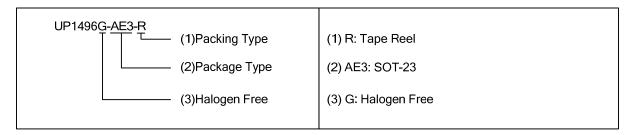
### **■** DESCRIPTION

The UTC **UP1496** are series of PNP silicon planar transistors which have gain of 500 at  $I_{\rm C}$ =100mA. It can be used in such applications like battery powered circuits and darlington replacements.



#### ■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Dooking	
		1	2	3	Packing	
UP1496G-AE3-R	SOT-23	Е	В	С	Tape Reel	



#### ■ MARKING



## ■ ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT	
Collector-Base Voltage	$V_{CBO}$	-220	V	
Collector-Emitter Voltage	$V_{CEO}$	-200	V	
Emitter-Base Voltage	$V_{EBO}$	-5	V	
Collector Current	Ic	-0.3	Α	
Peak Pulse Current	I <sub>CM</sub>	-1	Α	
Base Current	Ι <sub>Β</sub>	-200	mA	
Collector Dissipation (T <sub>a</sub> =25°C)	Pc	500	mW	
Junction Temperature	$T_J$	+150	°C	
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

## ■ **ELECTRICAL CHARACTERISTICS** (T<sub>a</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$BV_CBO$	I <sub>C</sub> =-100 μA	-220			V
Collector-Emitter Breakdown Voltage	$BV_CEO$	I <sub>C</sub> =-10 mA (Note)	-200			٧
Emitter-Base Breakdown Voltage	$BV_{EBO}$	I <sub>E</sub> =-100 μA	-5			V
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =-200 V			-100	nA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =-4 V			-100	nA
Collector -Emitter Cut-off Current	I <sub>CES</sub>	V <sub>CES</sub> =-200 V			-100	nA
DC Current Transfer Ratio	h <sub>FE</sub>	$V_{CE}$ =-10V , $I_{C}$ =-1mA	100			
		V <sub>CE</sub> =-10V , I <sub>C</sub> =-100mA (Note)	100			
		V <sub>CE</sub> =-10V , I <sub>C</sub> =-250mA (Note)	85		300	
		V <sub>CE</sub> =-10V , I <sub>C</sub> =-400mA (Note)	35			
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	V <sub>CE</sub> =-10V , I <sub>C</sub> =-250 mA (Note)			-0.9	<b>V</b>
Collector-Emitter Saturation Voltage	$V_{\text{CE(SAT)}}$	I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA			-0.2	٧
		I <sub>C</sub> =-250mA, I <sub>B</sub> =-25mA (Note)			-0.35	٧
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I <sub>C</sub> =-250mA, I <sub>B</sub> =-25mA (Note)			-1.0	<b>V</b>
Transition Frequency	f <sub>T</sub>	$V_{CE}$ =-10V , $I_{C}$ =-50mA, f=100MHz	150			MHz
Output Capacitance	Сов	V <sub>CB</sub> =-10V, f=1MHz			10	рF

Note: Measured under pulse conditions. Pulse width=300 $\mu$ s. Duty cycle  $\leq$  2%.

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